

Stephen A Lyon

List of Publications by Year in descending order

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67

papers

5,433

citations

101384

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68

times ranked

5907

citing authors

#	ARTICLE	IF	CITATIONS
1	Optically Detected Magnetic Resonance in Neutral Silicon Vacancy Centers in Diamond via Bound Exciton States. <i>Physical Review Letters</i> , 2020, 125, 237402.	2.9	36
2	New Host Materials for Rare Earth Ions. , 2020, , .	0	
3	Electron Spin Resonance of P Donors in Isotopically Purified Si Detected by Contactless Photoconductivity. <i>Physical Review Applied</i> , 2019, 11, .	1.5	4
4	Narrow Optical Line Widths in Erbium Implanted in TiO ₂ . <i>Nano Letters</i> , 2019, 19, 8928-8933.	4.5	30
5	Thermopower-Based Hot Electron Thermometry of Helium Surface States at 1.6ÅK. <i>Physical Review Letters</i> , 2018, 121, 236801.	2.9	3
6	Observation of an environmentally insensitive solid-state spin defect in diamond. <i>Science</i> , 2018, 361, 60-63.	6.0	173
7	Annealing shallow Si/SiO ₂ interface traps in electron-beam irradiated high-mobility metal-oxide-silicon transistors. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	32
8	All-electric control of donor nuclear spin qubits in silicon. <i>Nature Nanotechnology</i> , 2017, 12, 958-962.	15.6	47
9	NLRP3 activation and mitosis are mutually exclusive events coordinated by NEK7, a new inflammasome component. <i>Nature Immunology</i> , 2016, 17, 250-258.	7.0	532
10	Spin relaxation and donor-acceptor recombination of Se_{Si} in 28-silicon. <i>Physical Review B</i> , 2015, 92, .	1.1	10
11	Electron Spin Coherence of Shallow Donors in Natural and Isotopically Enriched Germanium. <i>Physical Review Letters</i> , 2015, 115, 247601.	2.9	35
12	Comparison of predicted and actual consequences of missense mutations. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2015, 112, E5189-98.	3.3	200
13	Real-time resolution of point mutations that cause phenovariance in mice. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2015, 112, E440-9.	3.3	75
14	Hybrid optical-electrical detection of donor electron spins with bound excitons in silicon. <i>Nature Materials</i> , 2015, 14, 490-494.	13.3	29
15	Fast, low-power manipulation of spin ensembles in superconducting microresonators. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	63
16	Atomic clock transitions in silicon-based spin qubits. <i>Nature Nanotechnology</i> , 2013, 8, 561-564.	15.6	194
17	Electrical activation and electron spin resonance measurements of implanted bismuth in isotopically enriched silicon-28. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	47
18	Decoherence mechanisms of Bi_{Si} . <i>Physical Review B</i> , 2012, 86, .	1.1	27

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19	Observation of Rabi Splitting from Surface Plasmon Coupled Conduction State Transitions in Electrically Excited InAs Quantum Dots. <i>Nano Letters</i> , 2011, 11, 338-342.	4.5	25
20	Embracing the quantum limit in silicon computing. <i>Nature</i> , 2011, 479, 345-353.	13.7	228
21	Efficient Clocked Electron Transfer on Superfluid Helium. <i>Physical Review Letters</i> , 2011, 107, 266803.	2.9	32
22	Electrically Detected Magnetic Resonance of Neutral Donors Interacting with a Two-Dimensional Electron Gas. <i>Physical Review Letters</i> , 2011, 106, 207601. <i>Coherent State Transfer between an Electron and Nuclear Spin in</i> N^{15} <i>Physical Review Letters</i> , 2011, 106, 110504.	2.9	25
23	C_{60}^{13} <i>Physical Review Letters</i> , 2011, 106, 110504.	2.9	34
24	Mid-infrared surface plasmon coupled emitters utilizing intersublevel transitions in InAs quantum dots. <i>Proceedings of SPIE</i> , 2010, , .	0.8	0
25	Electron spin coherence of phosphorus donors in silicon: Effect of environmental nuclei. <i>Physical Review B</i> , 2010, 82, .	1.1	76
26	Mid-infrared Electroluminescence from Surface Plasmon Coupled InAs Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1208, 1.	0.1	0
27	Solid-state quantum memory using the ^{31}P nuclear spin. <i>Nature</i> , 2008, 455, 1085-1088.	13.7	351
28	Deterministic error model for quantum computer simulation. <i>Physical Review A</i> , 2008, 77, .	1.0	5
29	Spin-dependent scattering off neutral antimony donors in Si ₂₈ field-effect transistors. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	39
30	Electrical activation and electron spin coherence of ultralow dose antimony implants in silicon. <i>Applied Physics Letters</i> , 2006, 88, 112101.	1.5	69
31	Davies electron-nuclear double resonance revisited: Enhanced sensitivity and nuclear spin relaxation. <i>Journal of Chemical Physics</i> , 2006, 124, 234508.	1.2	33
32	Towards a fullerene-based quantum computer. <i>Journal of Physics Condensed Matter</i> , 2006, 18, S867-S883.	0.7	138
33	The N@C ₆₀ nuclear spin qubit: Bang-bang decoupling and ultrafast phase gates. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 3028-3031.	0.7	30
34	Bang-bang control of fullerene qubits using ultrafast phase gates. <i>Nature Physics</i> , 2006, 2, 40-43.	6.5	174
35	Electron spin coherence in Si. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 35, 257-263.	1.3	24
36	Spin Relaxation in SiGe Islands. <i>Materials Research Society Symposia Proceedings</i> , 2006, 958, 1.	0.1	0

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37	Stark Tuning of Donor Electron Spins in Silicon. Physical Review Letters, 2006, 97, 176404.	2.9	73
38	Spin Manipulation of Free Two-Dimensional Electrons in Si/SiGe Quantum Wells. Physical Review Letters, 2005, 94, 126802.	2.9	85
39	High Fidelity Single Qubit Operations Using Pulsed Electron Paramagnetic Resonance. Physical Review Letters, 2005, 95, 200501.	2.9	77
40	6 nm half-pitch lines and 0.04 Åum ² static random access memory patterns by nanoimprint lithography. Nanotechnology, 2005, 16, 1058-1061.	1.3	142
41	Negative differential Rashba effect in two-dimensional hole systems. Applied Physics Letters, 2004, 85, 3151-3153.	1.5	29
42	Fabrication of 5nm linewidth and 14nm pitch features by nanoimprint lithography. Applied Physics Letters, 2004, 84, 5299-5301.	1.5	564
43	Picosecond electrical excitation of a two-dimensional electron gas. , 2004, , .		2
44	Relaxation of candidate electron spin qubits. , 2004, 5472, 97.		1
45	Mid-infrared photoconductivity in InAs quantum dots. Applied Physics Letters, 1997, 70, 1861-1863.	1.5	183
46	Optimally designed potentials for control of electron-wave scattering in semiconductor nanodevices. Physical Review B, 1994, 49, 11100-11110.	1.1	30
47	Silicide/strained Si _{1-x} Ge _x / Schottky-barrier infrared detectors. IEEE Electron Device Letters, 1993, 14, 199-201.	2.2	63
48	Simple method to start and maintain self-mode-locking of a Ti:sapphire laser. Optics Letters, 1992, 17, 1219.	1.7	40
49	Observation of hot-electron energy loss through the emission of phonon-plasmon coupled modes in GaAs. Physical Review Letters, 1990, 65, 760-763.	2.9	49
50	Mid-infrared reflectivity and ellipsometry measurements on single-crystal YBa ₂ Cu ₃ O ₇ and Bi ₂ Sr ₂ CuO _{6+y} . Physical Review B, 1989, 40, 6884-6889.	1.1	28
51	Relationship between trapped holes, positive ions, and interface states in irradiated Si-SiO ₂ structures. Applied Physics Letters, 1989, 55, 2328-2330.	1.5	35
52	Voltage tunable quantum well infrared detector. Applied Physics Letters, 1989, 55, 2417-2419.	1.5	61
53	Electroluminescence of ballistically injected electrons in AlGaAs/GaAs heterodiodes. Physical Review Letters, 1989, 63, 2849-2852.	2.9	33
54	Photovoltaic quantum well infrared detector. Applied Physics Letters, 1988, 52, 1701-1703.	1.5	55

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55	Relationship between hole trapping and interface state generation in metal-oxide-silicon structures. Applied Physics Letters, 1988, 52, 1431-1433.	1.5	93
56	Performance aspects of a quantum-well detector. Journal of Applied Physics, 1988, 63, 5149-5153.	1.1	35
57	Grating enhancement of quantum well detector response. Applied Physics Letters, 1988, 53, 1027-1029.	1.5	49
58	Cycling of defects between trapped negative charge and interface states at the Si-SiO ₂ interface. Applied Physics Letters, 1987, 50, 1152-1154.	1.5	27
59	Spectroscopy of hot carriers in semiconductors. Journal of Luminescence, 1986, 35, 121-154.	1.5	240
60	Location of positive charge trapped near the Si-SiO ₂ interface at low temperature. Applied Physics Letters, 1986, 48, 136-138.	1.5	53
61	Amphoteric defects at the Si-SiO ₂ interface. Applied Physics Letters, 1986, 48, 662-664.	1.5	72
62	Hot-Electron Relaxation in GaAs Quantum Wells. Physical Review Letters, 1985, 55, 2359-2361.	2.9	137
63	New model of the rapid initial oxidation of silicon. Applied Physics Letters, 1985, 47, 154-156.	1.5	34
64	Grating enhanced quantum well detector. Applied Physics Letters, 1985, 47, 1257-1259.	1.5	106
65	Capture and tunnel emission of electrons by deep levels in ultrathin nitrided oxides on silicon. Applied Physics Letters, 1984, 44, 316-318.	1.5	101
66	Role of Electromagnetic Resonances in the Surface-Enhanced Raman Effect. Physical Review Letters, 1983, 51, 593-596.	2.9	38
67	Microstrain in laser-crystallized silicon islands on fused silica. Applied Physics Letters, 1982, 40, 316-318.	1.5	67